

2SJ247

Silicon P Channel MOS FET

REJ03G0854-0200
(Previous: ADE-208-1188)
Rev.2.00
Sep 07, 2005

Description

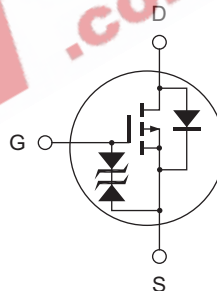
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for switching regulator, DC-DC converter

Outline

RENESAS Package code: PRSS0004AC-A
(Package name: TO-220AB)



1. Gate
2. Drain (Flange)
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	-8	A
Drain peak current	I _{D (pulse)} ^{Note 1}	-32	A
Body to drain diode reverse drain current	I _{DR}	-8	A
Channel dissipation	P _{ch} ^{Note 2}	40	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value at Tc = 25°C

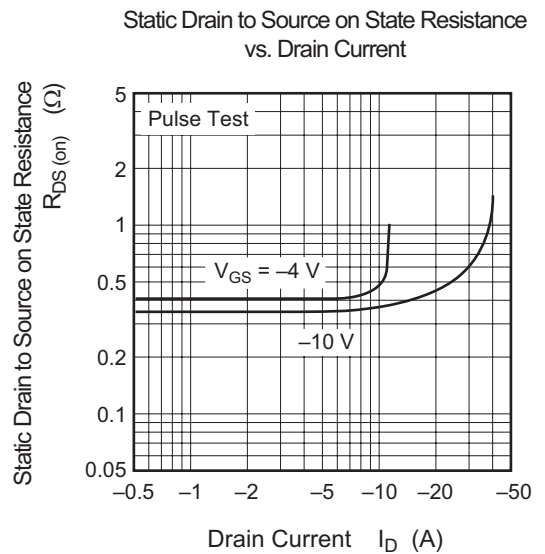
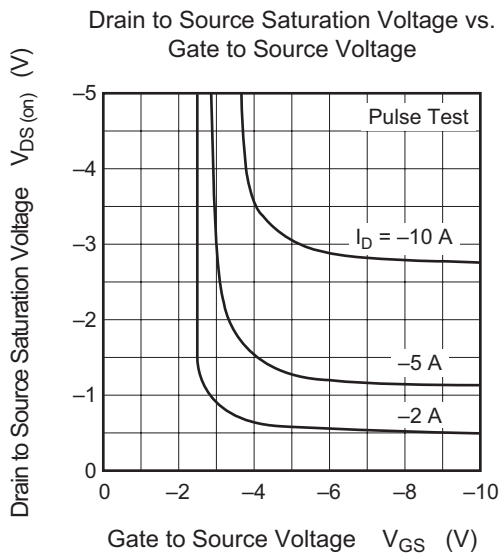
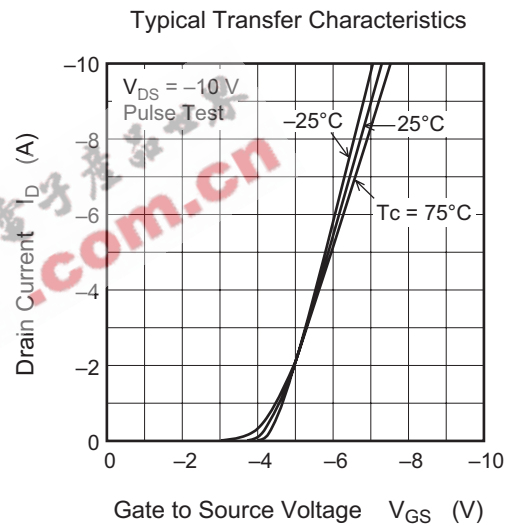
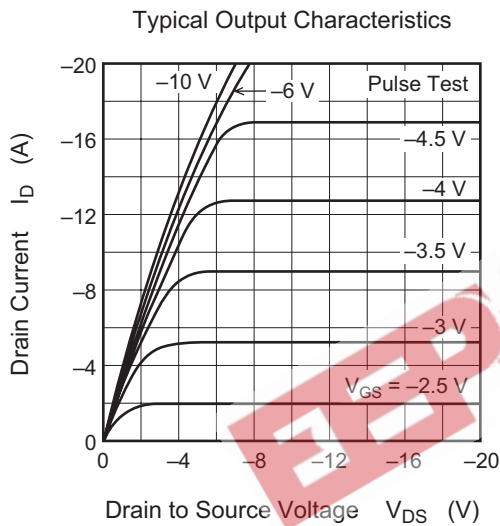
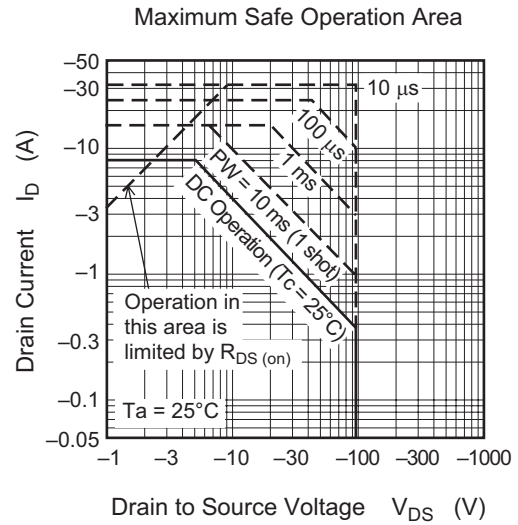
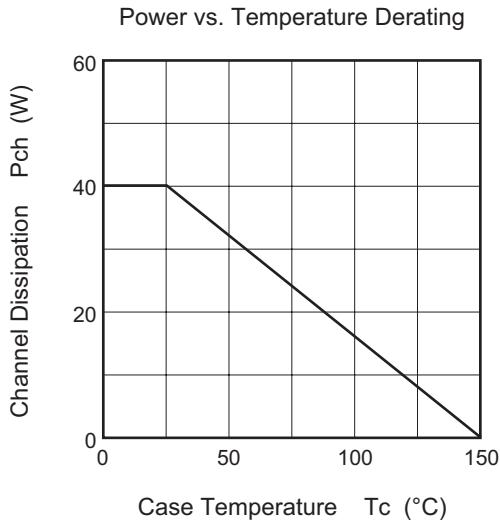
Electrical Characteristics

(Ta = 25°C)

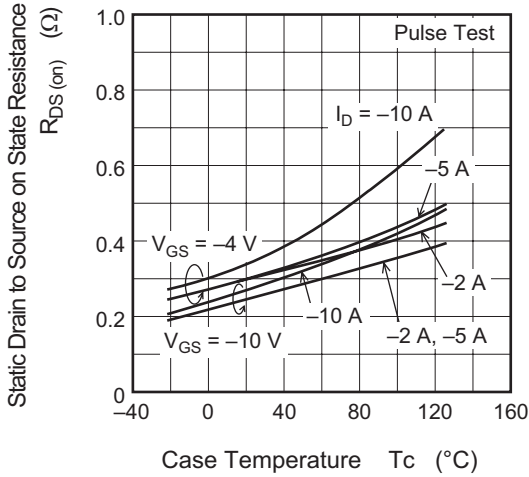
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	-100	—	—	V	I _D = -10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	-250	μA	V _{DS} = -80 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS (off)}	-1.0	—	-2.0	V	I _D = -1 mA, V _{DS} = -10 V
Static drain to source on state resistance	R _{DS (on)}	—	0.25	0.3	Ω	I _D = -4 A, V _{GS} = -10 V ^{Note 3}
	R _{DS (on)}	—	0.3	0.45	Ω	I _D = -4 A, V _{GS} = -4 V ^{Note 3}
Forward transfer admittance	y _{fs}	3.0	5.5	—	S	I _D = -4 A, V _{DS} = -10 V ^{Note 3}
Input capacitance	C _{iSS}	—	880	—	pF	V _{DS} = -10 V
Output capacitance	C _{oSS}	—	325	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rSS}	—	80	—	pF	f = 1 MHz
Turn-on delay time	t _{d (on)}	—	12	—	ns	I _D = -4 A
Rise time	t _r	—	47	—	ns	V _{GS} = -10 V
Turn-off delay time	t _{d (off)}	—	150	—	ns	R _L = 7.5 Ω
Fall time	t _f	—	75	—	ns	
Body to drain diode forward voltage	V _{DF}	—	-1.0	—	V	I _F = -8 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	170	—	ns	I _F = -8 A, V _{GS} = 0 di _F /dt = 50 A/μs

Note: 3. Pulse test

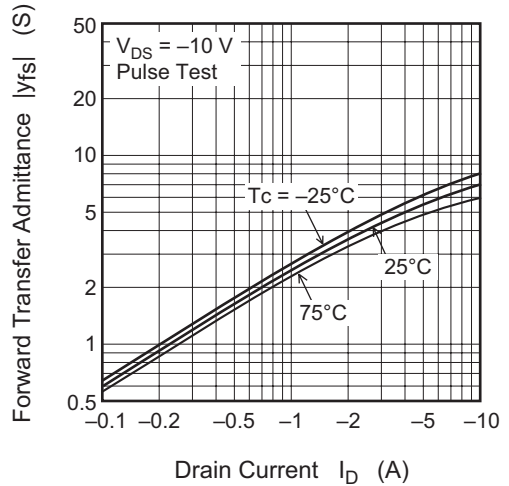
Main Characteristics



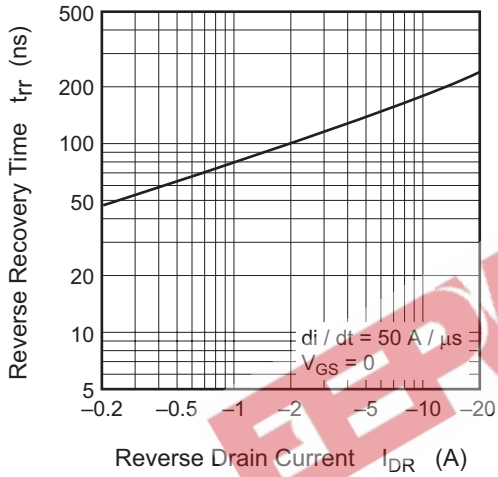
Static Drain to Source on State Resistance vs. Temperature



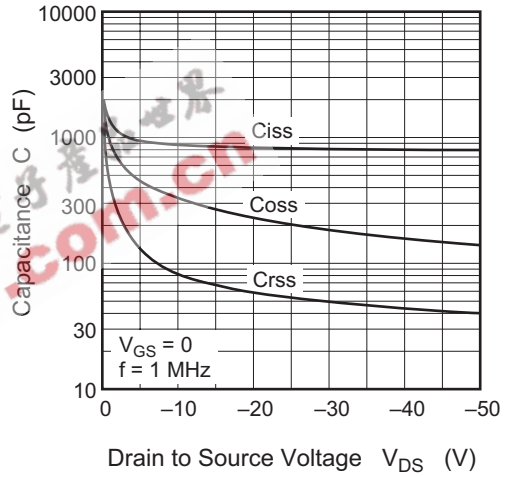
Forward Transfer Admittance vs. Drain Current



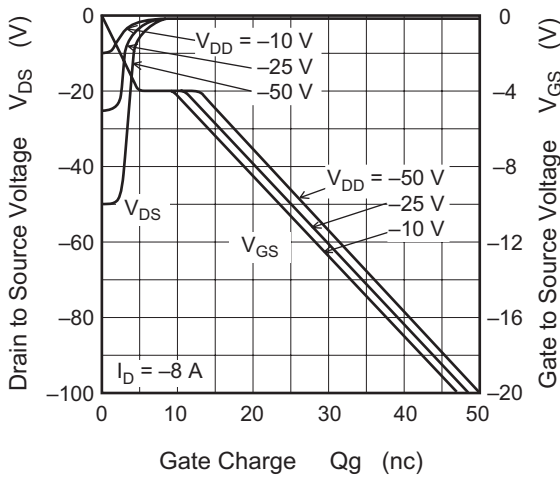
Body-Drain Diode Reverse Recovery Time



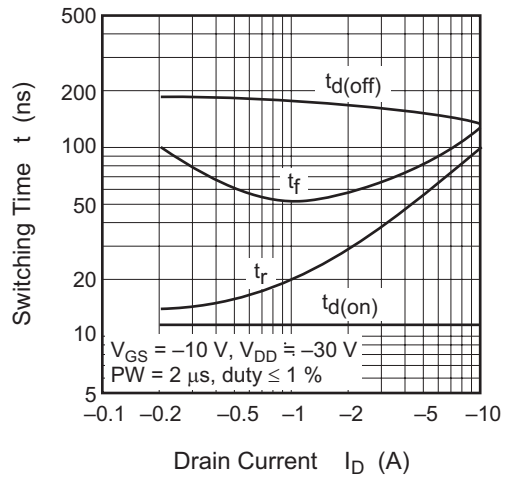
Typical Capacitance vs. Drain to Source Voltage



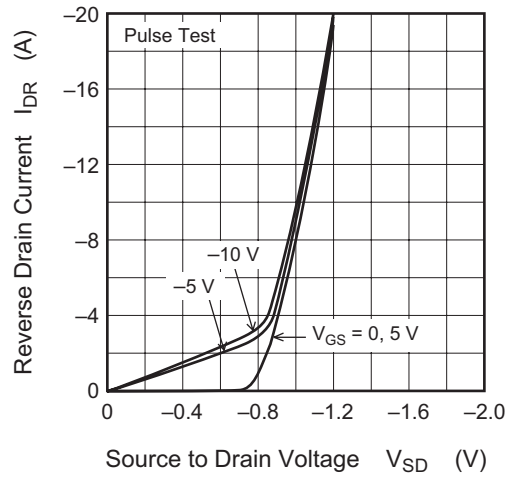
Dynamic Input Characteristics



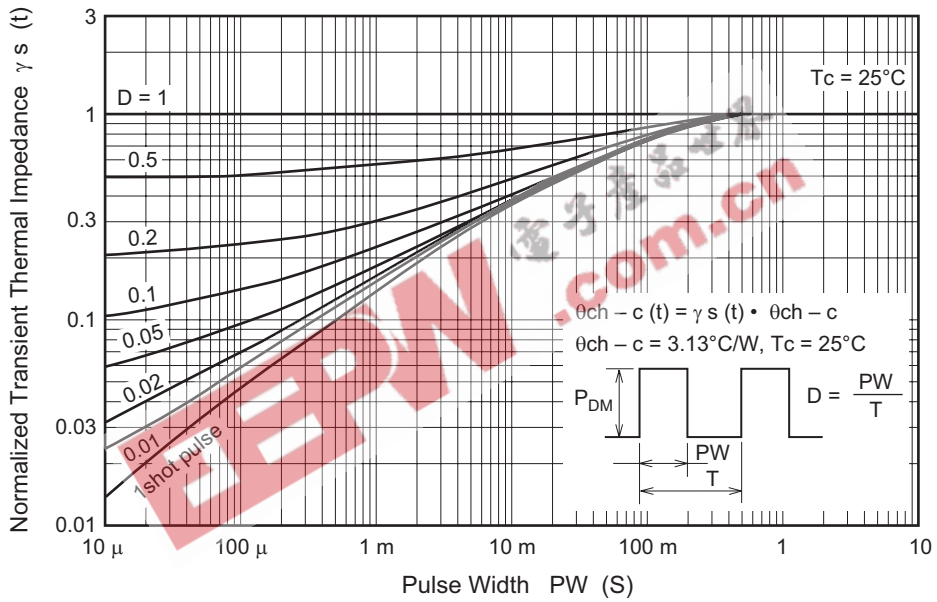
Switching Characteristics



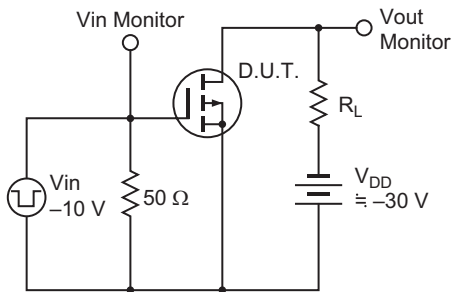
Reverse Drain Current vs. Source to Drain Voltage



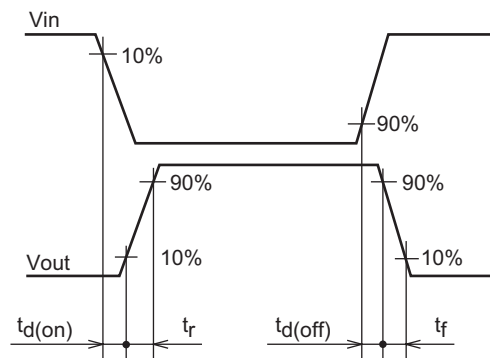
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit



Waveform



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